

# 6 to 18 GHz AA618L2-00 GaAs MMIC Amplifier

T-74-13-a

## Features

- Feedback Design
- Excellent Broadband Performance
- Includes I/O DC Blocks
- Low DC Power Consumption
- E-Beam Written Gate for Uniformity with High Performance
- On Wafer Probe Pads
- Size: 92 x 92 x 6

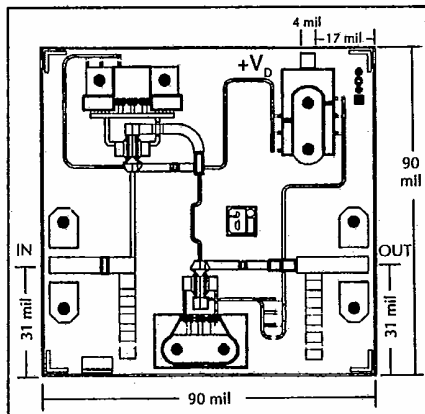
## Description

The AA618L2-00 features two 0.5 x 300 micron ion-implanted MESFET devices with E-beam written gates for excellent uniformity and reproducibility. Series and shunt feedback design techniques give improved gain flatness and input/output VSWR. These features result in an easily cascadable chip. Single and dual bias options are available to satisfy a variety of applications.

## Electrical Specifications

Frequency .....	6 to 18 GHz
Small Signal Gain .....	8 dB, Typ.
Flatness .....	$\pm 0.75$ , Typ. $\pm 1.0$ , Max.
Input/Output VSWR .....	2:1, Typ. 2.2:1, Max.
Noise Figure .....	7.5 dB, Max.
$P_{1dB}$ .....	10 dBm, Typ.
$I_{ds}$ , at $V_{ds}=3V$ and $V_{gs}=-1V$ .....	80 mA Typ., 100 mA Max.

## Chip Configuration



## Typical Performance

